



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SD669**2SD669A**

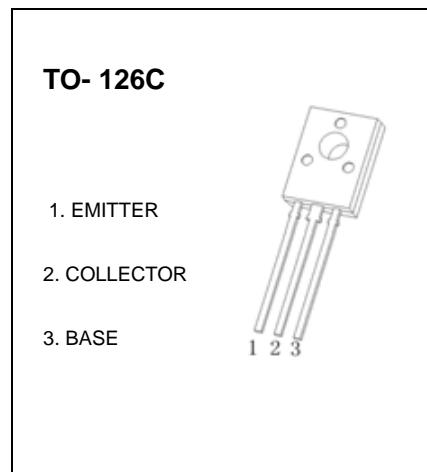
TRANSISTOR (NPN)

FEATURES

Low Frequency Power Amplifier Complementary Pair
with 2SB649/A

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector- Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage 2SD669 2SD669A	120 160	V
V _{EBO}	Emitter-Base Voltage	5	V
I _c	Collector Current -Continuous	1.5	A
P _c	Collector Dissipation	1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

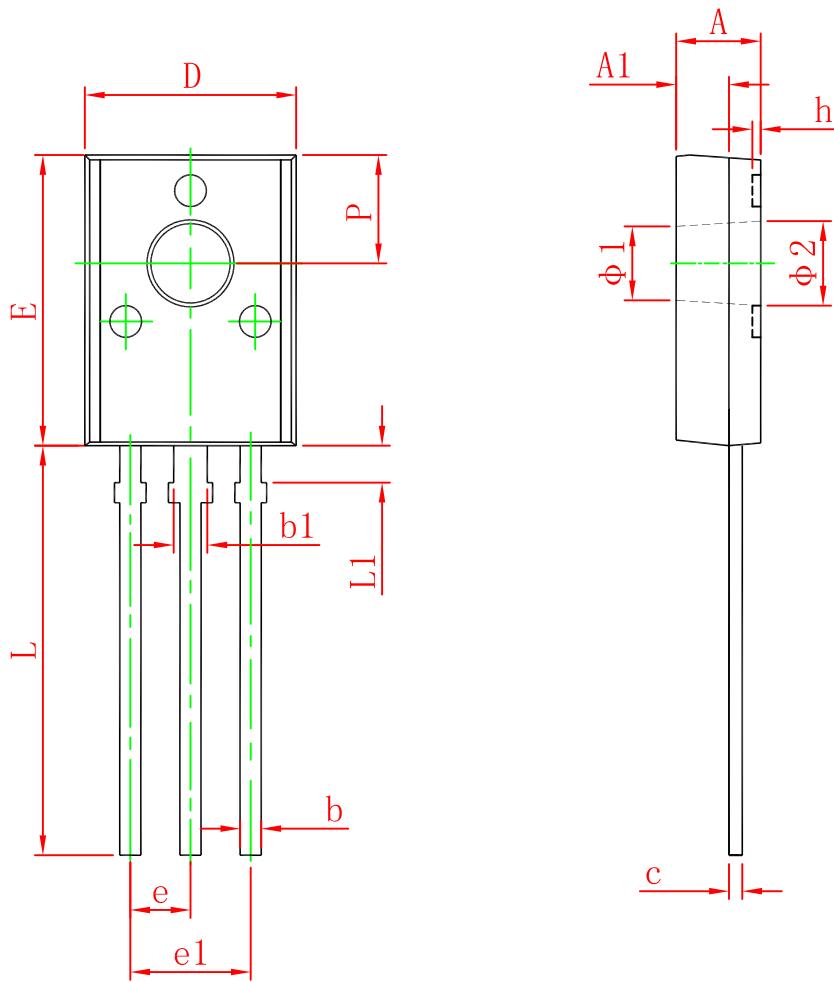
**ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	180			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0 2DS669 2SD669A	120 160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =160V, I _E =0			10	µA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			10	µA
DC current gain	h _{FE(1)}	V _{CE} =5V, I _C =150mA 2SD669 2SD669A	60 60		320 200	
	h _{FE(2)}	V _{CE} =5V, I _C =500mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA			1	V
Base-emitter voltage	V _{BE}	V _{CE} =5V, I _C =150mA			1.5	V
Transition frequency	f _T	V _{CE} =5V, I _C =150mA		140		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		14		pF

CLASSIFICATION OF h_{FE(1)}

Rank	B	C	D
Range 2SD669	60-120	100-200	160-320
2SD669A	60-120	100-200	

TO-126C Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	3.000	3.400	0.118	0.134
A1	1.800	2.200	0.071	0.087
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.800	8.200	0.307	0.323
E	10.800	11.200	0.425	0.441
e	2.280 TYP.		0.090 TYP.	
e1	4.460	4.660	0.176	0.183
L	15.300	15.700	0.602	0.618
L1	1.300	1.500	0.051	0.059
P	4.040	4.240	0.159	0.167
Φ1	2.700	2.900	0.106	0.114
Φ2	3.100	3.300	0.122	0.130

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